

WHAT IS CLAIMED IS:

1. A nitride semiconductor laser device, comprising:
a nitride semiconductor substrate; and
a layered portion corresponding to a nitride semiconductor film
grown on said nitride semiconductor substrate, said layered portion
5 including an n-type layer and a p-type layer and a light emitting layer posed
between said n- and p-type layers, of said n- and p-type layers a layer
opposite to said nitride semiconductor substrate with said light emitting
layer posed therebetween serving as an upper layer having a stripe of 1.9
10 μm to 3.0 μm in width, said light emitting layer and said upper layer having
an interface distant from a bottom of said stripe by 0 μm to 0.2 μm .
2. The nitride semiconductor laser device of claim 1, wherein said
layered portion and said nitride semiconductor substrate sandwich a low-
temperature buffer layer grown at a low temperature and thus formed.
3. The nitride semiconductor laser device of claim 1, wherein said
light emitting layer has one of P and As added thereto.
4. The nitride semiconductor laser device of claim 1, wherein of
said n- and p-type layers a layer closer to said nitride semiconductor
substrate serves as a lower layer including a crack prevention layer
containing In.
5. The nitride semiconductor laser device of claim 1, wherein said
light emitting layer starts with one of well and barrier layers, followed by
said well and barrier layers alternately stacked thereon, and ends with said
one of said well and barrier layers to have a multi-layered structure and said
5 light emitting layer is formed of a total of two to six layers.
6. The nitride semiconductor laser device of claim 2, wherein said
light emitting layer starts with one of well and barrier layers, followed by

said well and barrier layers alternately stacked thereon, and ends with said one of said well and barrier layers to have a multi-layered structure and said light emitting layer is formed of a total of two to six layers.

7. The nitride semiconductor laser device of claim 3, wherein said light emitting layer starts with one of well and barrier layers, followed by said well and barrier layers alternately stacked thereon, and ends with said one of said well and barrier layers to have a multi-layered structure and said light emitting layer is formed of a total of two to six layers.

8. The nitride semiconductor laser device of claim 4, wherein said light emitting layer starts with one of well and barrier layers, followed by said well and barrier layers alternately stacked thereon, and ends with said one of said well and barrier layers to have a multi-layered structure and said light emitting layer is formed of a total of two to six layers.

9. The nitride semiconductor laser device of claim 1, wherein said light emitting layer contains an impurity selected from the group consisting of Si, O, C, Ge, Zn and Mg.

10. The nitride semiconductor laser device of claim 2, wherein said light emitting layer contains an impurity selected from the group consisting of Si, O, C, Ge, Zn and Mg.

11. The nitride semiconductor laser device of claim 3, wherein said light emitting layer contains an impurity selected from the group consisting of Si, O, C, Ge, Zn and Mg.

12. The nitride semiconductor laser device of claim 4, wherein said light emitting layer contains an impurity selected from the group consisting of Si, O, C, Ge, Zn and Mg.

13. The nitride semiconductor laser device of claim 5, wherein said

light emitting layer contains an impurity selected from the group consisting of Si, O, C, Ge, Zn and Mg.

14. The nitride semiconductor laser device of claim 6, wherein said light emitting layer contains an impurity selected from the group consisting of Si, O, C, Ge, Zn and Mg.

15. The nitride semiconductor laser device of claim 7, wherein said light emitting layer contains an impurity selected from the group consisting of Si, O, C, Ge, Zn and Mg.

16. The nitride semiconductor laser device of claim 1, wherein said upper layer includes a carrier block layer containing Al.

17. The nitride semiconductor laser device of claim 3, wherein said upper layer includes a carrier block layer containing Al.

18. An optical pickup apparatus comprising the nitride semiconductor laser device as recited in claim 1.